

ABSTRACT

A memory (1) is provided with: an address control portion (10); a protection film (11); a property deterioration material layer 5 (12); data storage areas (14, 15, 16, 17); and bonding pads (18). The protection film (11) protects an organic semiconductor layer constituting a semiconductor circuit and prevents intrusion of moisture or chemical molecules in the air, light, or the like, into the organic semiconductor layer. Deterioration of the organic 10 semiconductor layer is started by breaking the protection film (11) and using a specified means, thus starting operation of the lifetime period. Furthermore, the property deterioration material layer (12) contains a material for deteriorating the property of the organic semiconductor and deterioration of the organic semiconductor layer 15 is started by diffusing the material into the organic semiconductor layer.